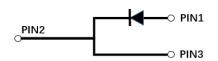




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I F (135°C)	3.7A
Qc	13.7nC





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112002DG1
Reverse voltage (Repetitive peak) @ Tj=25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	٧	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	٧	1200
Continuous forward current @ T _C =25°C			7.6
Continuous forward current @ T _C =135°C	I _F	A	3.7
Continuous forward current @ T _C =160°C			2
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	29
Power Dissipation@ T _C =25°C	Б	w	40
Power Dissipation@ T _C =110°C	P _{TOT}		17
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	4.2
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
Famuerd voltage drap	V _F	V	I _F =2A, T _j =25°C	1.36	1.55		
Forward voltage drop			I _F =2A, T _j =175°C	2.0	-		
Deverse legicage gurrent	I _R μA	V _R =1200V, T _j =25°C	0.5	10			
Reverse leakage current		μΑ	V _R =1200V, T _j =175°C	10	-		
Total capacitive charge	Q _C	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{VR}C(V)dV$	13.7	-		
					V _R =0V, f=1MHZ	183	-
Total capacitance C	С	pF	V _R =400V, f=1MHZ	13	-		
			V _R =800V, f=1MHZ	10	-		
Capacitance Stored Energy	Ec	μJ	V _R =800V	3.5	-		

■Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	3.67

■Typical Characteristics

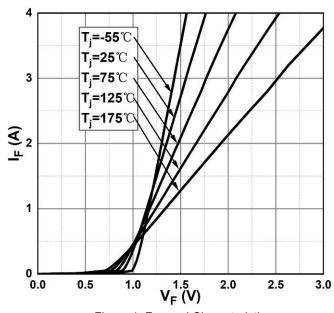


Figure 1. Forward Characteristics

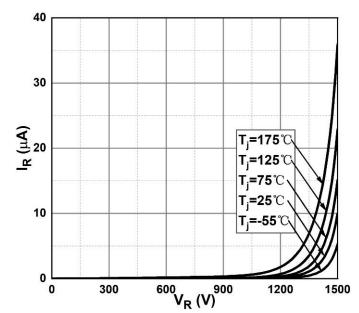
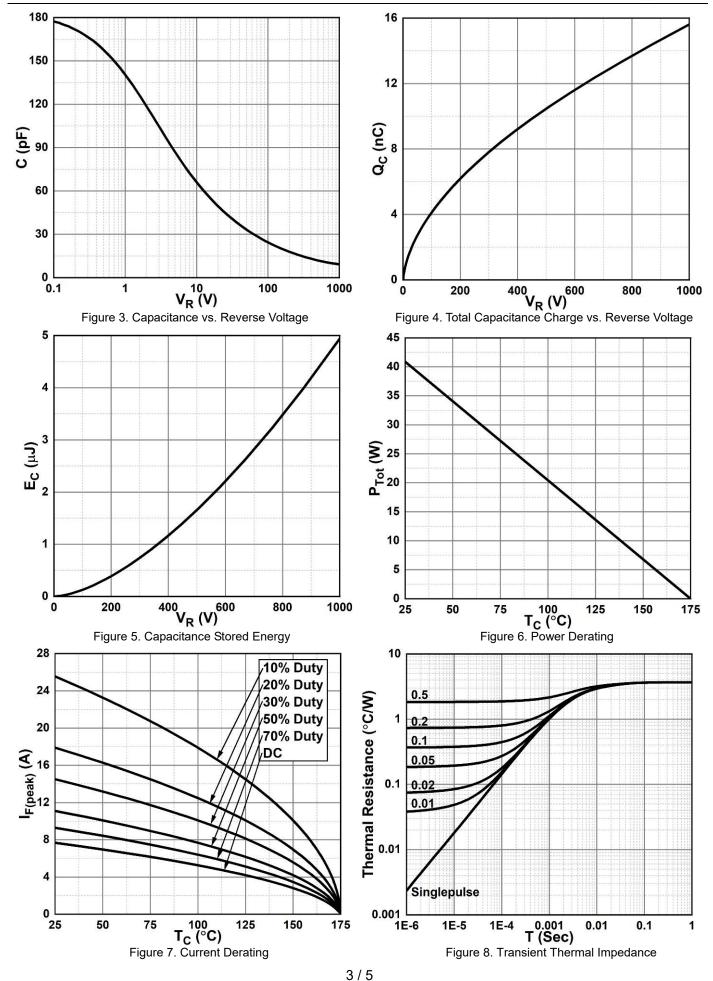


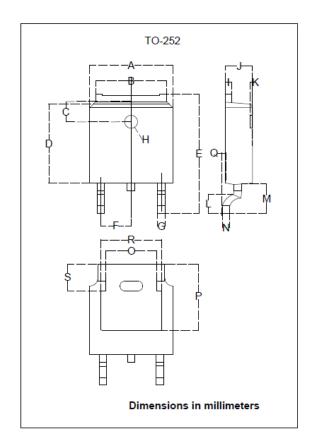
Figure 2. Reverse Characteristics







■Outline Dimensions



TO-252		
Dim	Min	Max
Α	6.500	6.700
В	5.100	5.460
С	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
Н	Ф1.050	Ф1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.730	3.080
N	0.430	0.580
0	4.20	4.95
Р	5.15	5.45
Q	0	0.2
R	4.50	5.10
S	1.60	2.40



YJD112002DG1Q



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